



ELECTRONICS, INC.
 44 FARRAND STREET
 BLOOMFIELD, NJ 07003
 (973) 748-5089
<http://www.nteinc.com>

MPSA28

Silicon NPN Transistor

Darlington, General Purpose Amplifier,

TO-92 Type Package

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$, Note 1 unless otherwise specified)

| | |
|---|-------------------------------------|
| Collector–Emitter Voltage, V_{CES} | 80V |
| Collector–Base Voltage, V_{CBO} | 80V |
| Emitter–Base Voltage, V_{EBO} | 12V |
| Continuous Collector Current, I_C | 800mA |
| Total Device Dissipation ($T_A = +25^\circ\text{C}$), P_D | 625mW |
| Derate Above 25°C | 5mW/ $^\circ\text{C}$ |
| Operating Junction Temperature Range, T_J | -55° to $+150^\circ\text{C}$ |
| Storage Temperature Range, T_{stg} | -55° to $+150^\circ\text{C}$ |
| Thermal Resistance, Junction–to–Case, R_{thJC} | 83.3 $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction–to–Ambient, R_{thJA} | 200 $^\circ\text{C}/\text{W}$ |

Note 1. These ratings are limiting values above which the serviceability of any semiconductor device may be impaired. These are steady state limits and based on a maximum junction temperature of $+150^\circ\text{C}$.

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|--------------------------------------|---------------|--|--------|-----|-----|------|
| OFF Characteristics | | | | | | |
| Collector–Emitter Breakdown Voltage | $V_{(BR)CES}$ | $I_C = 100\mu\text{A}$, $V_{BE} = 0$ | 80 | – | – | V |
| Collector–Base Breakdown Voltage | $V_{(BR)CBO}$ | $I_C = 100\mu\text{A}$, $I_E = 0$ | 80 | – | – | V |
| Emitter–Base Breakdown Voltage | $V_{(BR)EBO}$ | $I_E = 10\mu\text{A}$, $I_C = 0$ | 12 | – | – | V |
| Collector Cutoff Current | I_{CBO} | $V_{CB} = 60\text{V}$, $I_E = 0$ | – | – | 100 | nA |
| | I_{CES} | $V_{CE} = 60\text{V}$, $V_{BE} = 0$ | – | – | 500 | nA |
| Emitter Cutoff Current | I_{EBO} | $V_{EB} = 10\text{V}$, $I_C = 0$ | – | – | 100 | nA |
| ON Characteristics (Note 2) | | | | | | |
| DC Current Gain | h_{FE} | $I_C = 10\text{mA}$, $V_{CE} = 5\text{V}$ | 10,000 | – | – | |
| | | $I_C = 100\text{mA}$, $V_{CE} = 5\text{V}$ | 10,000 | – | – | |
| Collector–Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C = 10\text{mA}$, $I_B = 0.01\text{mA}$ | – | – | 1.2 | V |
| | | $I_C = 100\text{mA}$, $I_B = 0.1\text{mA}$ | – | – | 1.5 | V |
| Base–Emitter ON Voltage | $V_{BE(on)}$ | $I_C = 100\text{mA}$, $V_{CE} = 5\text{V}$ | – | – | 2.0 | V |
| Small Signal Characteristics | | | | | | |
| Current Gain – Bandwidth Product | f_T | $I_C = 10\text{mA}$, $V_{CE} = 5\text{V}$, $f = 100\text{MHz}$ | 125 | – | – | MHz |
| Output Capacitance | C_{obo} | $V_{CB} = 1\text{V}$, $I_E = 0$, $f = 1\text{MHz}$ | – | – | 8 | pF |

Note 2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

